Silicon NPN Power Transistors MJ4033/4034/4035

DESCRIPTION

·With TO-3 package
·Respectively complement to type
MJ4030/4031/4032
·DARLINGTON
·High DC current gain

APPLICATIONS

·For use as output devices in complementary general purpose amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

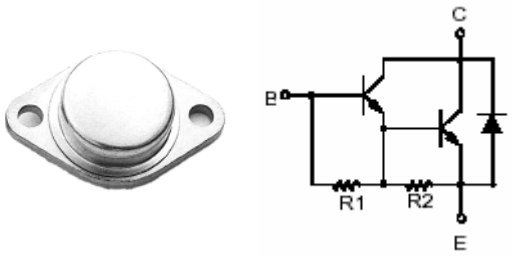


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(T_C=25□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	MJ4033	Open emitter	60	V
		MJ4034		80	
		MJ4035		100	
V_{CEO}	Collector-emitter voltage	MJ4033	Open base	60	V
		MJ4034		80	
		MJ4035		100	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			16	A
I_{CM}	Collector current-peak			20	A
I_B	Base current			0.5	A
P_C	Collector power dissipation		T_C=25□	150	W
T_j	Junction temperature			200	□
T_{stg}	Storage temperature			-65~200	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	MJ4033	I_C=0.1A ;I_B=0	60			V
		MJ4034		80			
		MJ4035		100			
$V_{CE(sat)-1}$	Collector-emitter saturation voltage		I_C=10A; I_B=40mA			2.5	V
$V_{CE(sat)-2}$	Collector-emitter saturation voltage		I_C=16A; I_B=80mA			4.0	V
V_{BE}	Base-emitter on voltage		I_C=10A ; V_{CE}=3V			3.0	V
I_{CEO}	Collector cut-off current		V_{CE}=30V; I_B=0			3.0	mA
			V_{CE}=40V; I_B=0				
			V_{CE}=50V; I_B=0				
I_{EBO}	Emitter cut-off current		V_{EB}=5V; I_C=0			5.0	mA
h_{FE}	DC current gain		I_C=10A ; V_{CE}=3V	1000			

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal resistance junction to case	1.17	□/W

PACKAGE OUTLINE

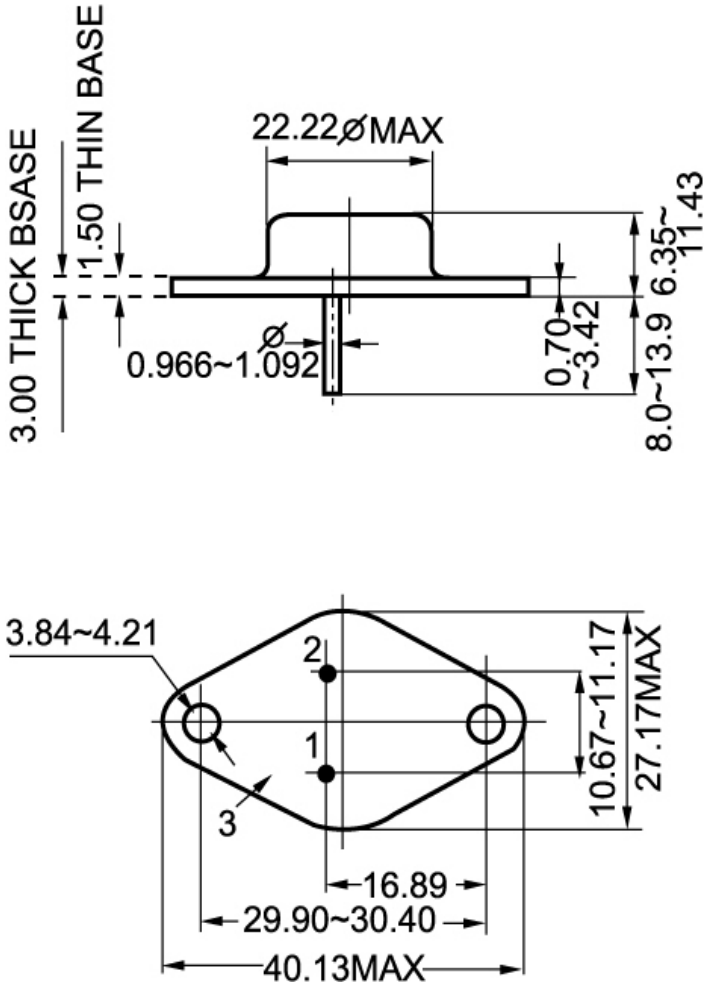


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)